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(71) Applicant: **APPLIED MATERIALS, INC.** [US/US];
3050 Bowers Avenue, Santa Clara, California 95054 (US).

(72) Inventors: **DING, Yi**; 3050 Bowers Avenue, Santa Clara,
California 95054 (US). **MUKHERJEE, Shaunak**; 3050
Bowers Avenue, Santa Clara, California 95054 (US). **XIE,
Bo**; 3050 Bowers Avenue, Santa Clara, California 95054
(US). **YIM, Kang Sub**; 3050 Bowers Avenue, Santa Clara,

California 95054 (US). **PADHI, Deenesh**; 3050 Bowers
Avenue, Santa Clara, California 95054 (US).

(74) Agent: **WRIGHT, Jonathan B.**; SERVILLA WHITNEY
LLC, 33 Wood Avenue South, Suite 830, Iselin, New Jersey
08830 (US).

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(54) Title: LOW-K DIELECTRIC WITH SELF-FORMING BARRIER LAYER

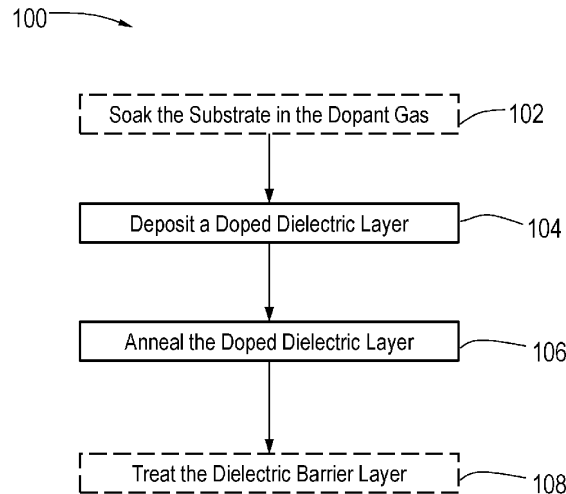


FIG. 1

(57) Abstract: A method of forming a low-k dielectric layer with barrier properties is disclosed. The method comprises forming a dielectric layer by PECVD which is doped with one or more of boron, nitrogen or phosphorous. The dopant gas of some embodiments may be coflowed with the other reactants during deposition.

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